

AMENDMENTS TO THE SUBSTITUTE SPECIFICATION:

Page 4 – Please replace the paragraph beginning on line 10 thereof with the amended paragraph as follows:

According to the above-described arrangement, the third and fourth transistors are configured as a vertical structure, the third transistor is laminated over the first transistor, and the fourth transistor is laminated over the second transistor. This achieves a reduction in cell area. The power supply circuit supplies the voltage, which is set on the condition that the difference between the source potential applied to each of the first and second transistors and the potential of the select level of the word line becomes greater than or equal to the threshold voltage of each of the third and fourth transistors, to the source electrode of each of the first and second transistors. Owing to this, "0" write compensation is carried out. This achieves the appropriateness of writing a logical value "0".

Page 15 – Please replace the paragraph beginning on line 20 thereof with the amended paragraph as follows:

A cross-section of a principal part of the 4T cell 300 is shown in Fig. 4. Incidentally, points designated at ~~←, ↗ and ↛~~ ~~①, ② and ③~~ in Figs. 3 and 4 are provided to facilitate a corresponding identification of the electrodes of the main transistors.